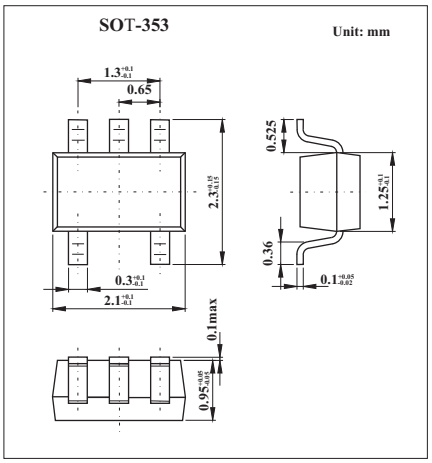
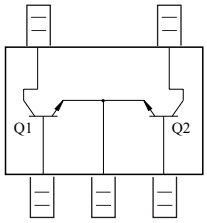
General purpose (Dual NPN Transistors)
KTC601U



■ Features

- Power dissipation: PC=200mW
- Collector Curren: IC=150mA



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current -Continuous	I_C	150	mA
Collector Power Dissipation(TOTAL)	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA, I_E=0	60			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1 mA， I_B=0	50			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E= 100 μA， I_C=0	5.0			V
Collector cutoff current	I_{CBO}	V_{CB}= 60 V , I_E=0			0.1	μA
Collector cutoff current	I_{EBO}	V_{CE}= 5.0V , I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}= 6V, I_C= 2.0mA	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B= 10mA			0.25	V
Transition frequency	f_T	V_{CE}= 10V, I_C= 1mA,f=100MHz	80			MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz			3.5	pF
Noise Figure	NF	V_{CE}=6V, I_C=0.1mA, f=1KHz , Rg=10KΩ		1	10	dB

■ hFE Classification

Marking	LY	LGR
Rank	Y	GR
Range	120～240	200～400